





45V PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ultra-low Profile (0.40mm max)
- Complementary NPN Type Available (BC847BLP4)
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)

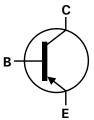
Mechanical Data

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0008 grams (approximate)

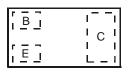
DFN1006H4-3



Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 3)

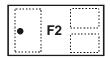
| Product | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|--------------|---------|--------------------|-----------------|-------------------|
| BC857BLP4-7 | F2 | 7 | 8 | 3,000 |
| BC857BLP4-7B | F2 | 7 | 8 | 10.000 |

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

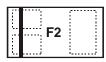
Marking Information

BC857BLP4-7



Top View Dot Denotes Collector Side

BC857BLP4-7B



Top View Bar Denotes Base and Emitter Side

F2 = Product Type Marking Code



Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -50 | V |
| Collector-Emitter Voltage | V_{CEO} | -45 | V |
| Emitter-Base Voltage | V_{EBO} | -5.0 | V |
| Collector Current | Ic | -100 | mA |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 4) @T _A = 25°C | P_{D} | 250 | mW |
| Thermal Resistance, Junction to Ambient Air (Note 4) @T _A = 25°C | $R_{	hetaJA}$ | 500 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

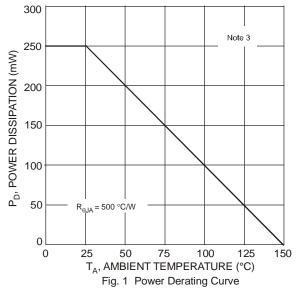
Electrical Characteristics @T_A = 25°C unless otherwise specified

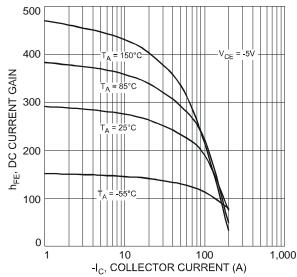
| Characteristic (Note 5) | Symbol | Min | Тур | Max | Unit | Test Condition |
|--------------------------------------|----------------------|-----------|--------------|--------------|----------|---|
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -50 | _ | _ | V | $I_C = 10\mu A, I_B = 0$ |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | -45 | _ | _ | V | $I_C = 10 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -5 | | 1 | > | $I_E = 1\mu A, I_C = 0$ |
| DC Current Gain | h _{FE} | 220 | 300 | 475 | | $V_{CE} = -5.0V, I_{C} = -2.0mA$ |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | -90 -250 | -300 -650 | mV | $I_C = -10$ mA, $I_B = -0.5$ mA $I_C = -100$ mA, $I_B = -5.0$ mA |
| Base-Emitter Saturation Voltage | V _{BE(SAT)} | _ | -700 -850 | 1 1 | mV | $I_C = -10$ mA, $I_B = -0.5$ mA $I_C = -100$ mA, $I_B = -5.0$ mA |
| Base-Emitter Voltage | V _{BE(ON)} | -600 — | -670 -710 | -750 -820 | mV | $V_{CE} = -5.0V$, $I_{C} = -2.0mA$ $V_{CE} = -5.0V$, $I_{C} = -10mA$ |
| Collector-Cutoff Current | I _{CBO} | _ | | -15 -4.0 | nΑ μΑ | V _{CB} = -30V V _{CB} = -30V, T _A = 150°C |
| Gain Bandwidth Product | f⊤ | 100 | | | MHz | $V_{CE} = -5.0V, I_{C} = -10mA,$ f = 100MHz |
| Collector-Base Capacitance | Ссво | _ | 3.0 | _ | pF | $V_{CB} = -10V, f = 1.0MHz$ |

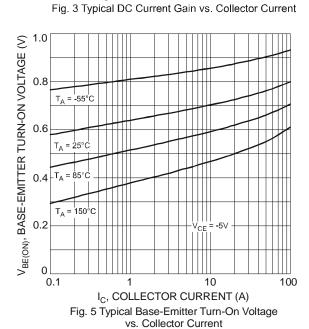
Notes:

^{4.} Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001 on our website at http://www.diodes.com 5. Short duration pulse test used to minimize self-heating effect.









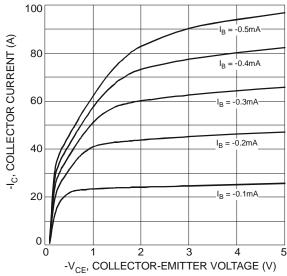
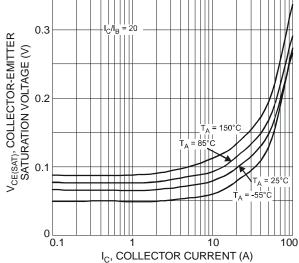


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



I_C, COLLECTOR CURRENT (A)
Fig. 4 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

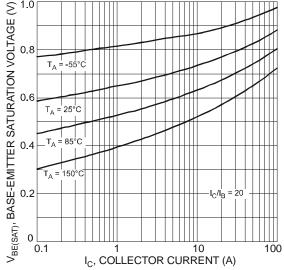
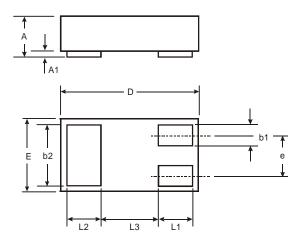


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

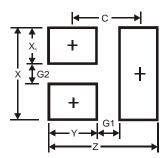


Package Outline Dimensions



| DFN1006H4-3 | | | | | |
|----------------------|------|-------|------|--|--|
| Dim | Min | Max | Тур | | |
| Α | _ | 0.40 | _ | | |
| A1 | 0 | 0.05 | 0.02 | | |
| b1 | 0.10 | 0.20 | 0.15 | | |
| b2 | 0.45 | 0.55 | 0.50 | | |
| D | 0.95 | 1.075 | 1.00 | | |
| E | 0.55 | 0.675 | 0.60 | | |
| е | _ | _ | 0.35 | | |
| L1 | 0.20 | 0.30 | 0.25 | | |
| L2 | 0.20 | 0.30 | 0.25 | | |
| L3 | _ | _ | 0.40 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 1.1 |
| G1 | 0.3 |
| G2 | 0.2 |
| Х | 0.7 |
| X1 | 0.25 |
| Y | 0.4 |
| С | 0.7 |



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